

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

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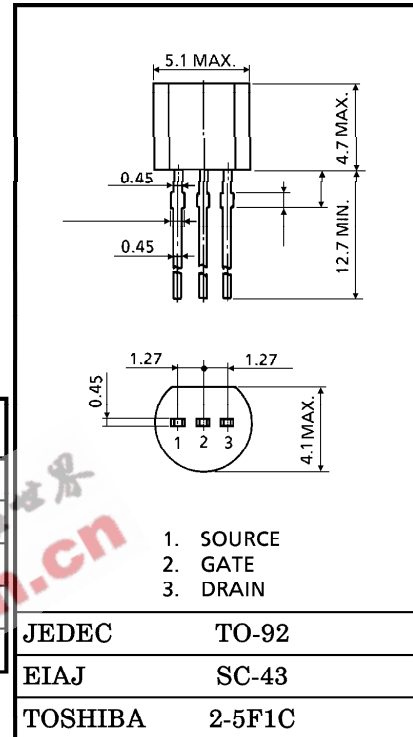
FOR CONSTANT CURRENT, IMPEDANCE
CONVERTER AND DC-AC HIGH INPUT
IMPEDANCE AMPLIFIER CIRCUIT APPLICATIONS

Unit in mm

- High Breakdown Voltage : $V_{GDS} = -50V$
- High Input Impedance : $I_{GSS} = 1nA (Max.) (V_{GS} = -30V)$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-50	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	300	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~125	$^\circ C$



Weight : 0.21g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

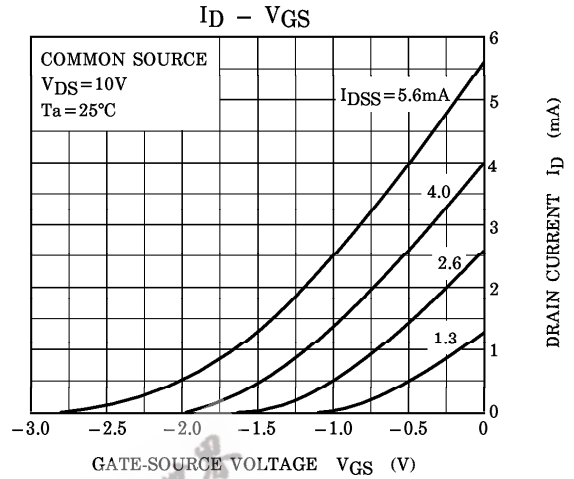
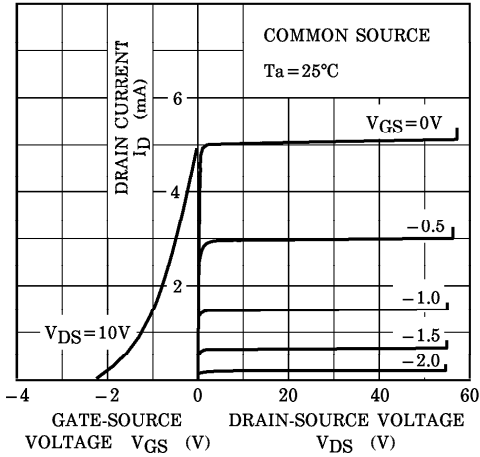
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I_{GSS}	$V_{GS} = -30V, V_{DS} = 0$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS} = 0, I_G = -100\mu A$	-50	—	—	V
Drain Current	I_{DSS} (Note)	$V_{DS} = 10V, V_{GS} = 0$	1.2	—	14	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 10V, I_D = 0.1\mu A$	-0.7	—	-6.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	1.5	—	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	9.0	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DG} = 10V, I_D = 0, f = 1MHz$	—	2.5	—	pF

Note : I_{DSS} Classification Y : 1.2~3.0mA, GR : 2.6~6.5mA, BL : 6~14mA

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STATIC CHARACTERISTICS



I_D - V_{DS} (LOW VOLTAGE REGION)

